研究室名

棚本研究室 学会発表

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演題名	Noise properties in the Coulomb blockade region of FinFET
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内容	A fin field-effect transistor (FinFET) is a promising candidate for the platform of a Si quantum computer. The noise properties of commercial FinFETs are investigated experimentally at a temperature of less than 10 K. The drain current shows a Coulomb oscillation, which indicates that the FinFET channel becomes a single quantum dot. The noise of the drain current is analyzed, and the basic properties of commercial FinFETs in the low-temperature region are discussed.